

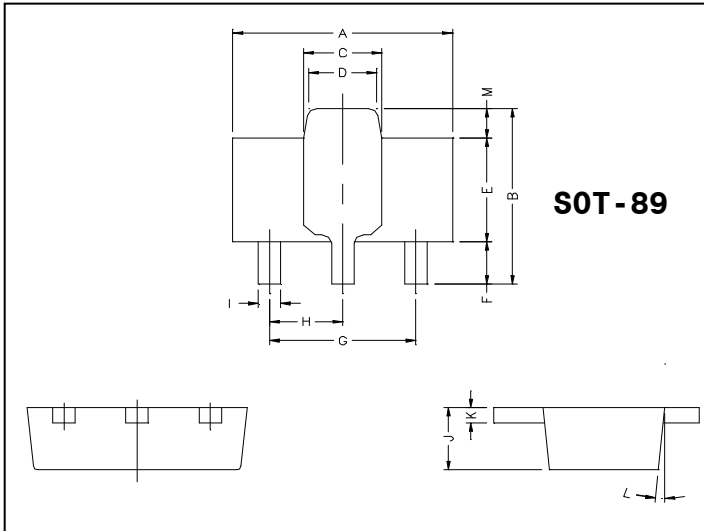
GM4033

PNP EPITAXIAL PLANAR TRANSISTOR

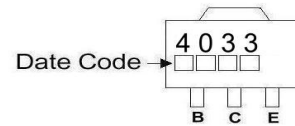
Description

The GM4033 is designed for high current general purpose amplifier applications .

Package Dimensions



Marking :



	Millimeter			Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00	REF.
B	4.05	4.25	H	1.50	REF.
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5° TYP.	
			M	0.70 REF.	

Absolute Maximum Ratings (Ta = 25°C, unless otherwise specified)

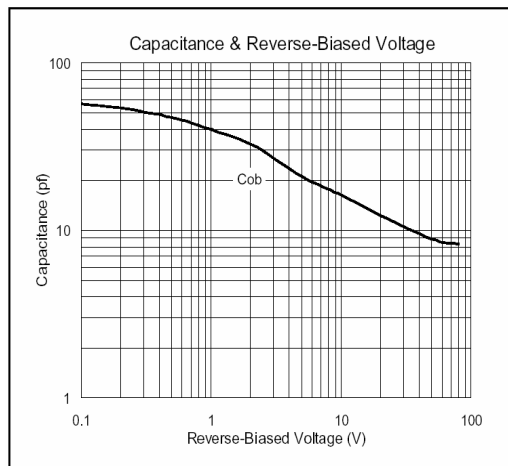
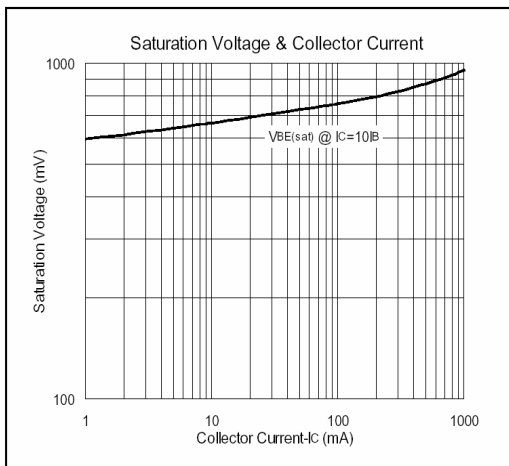
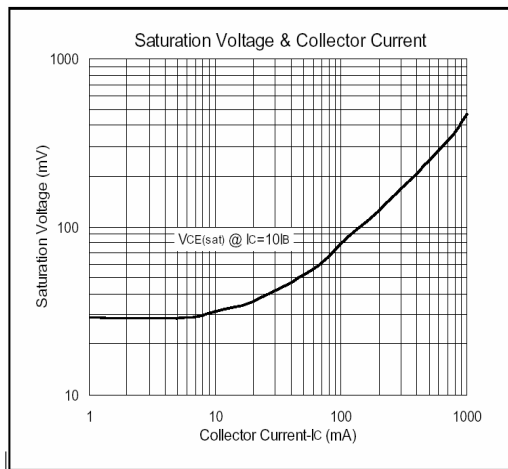
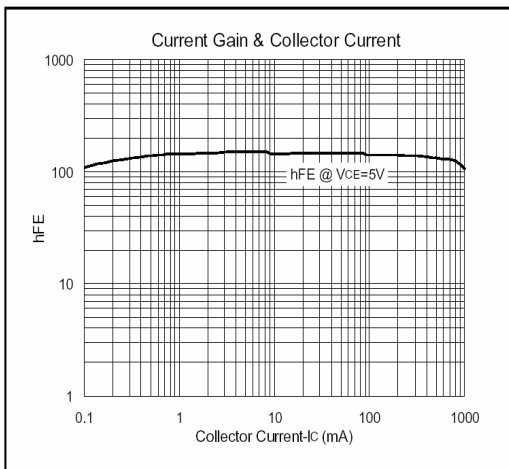
Parameter	Symbol	Ratings	Unit
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Collector to Base Voltage	V _{CB0}	-80	V
Collector to Emitter Voltage	V _{CE0}	-80	V
Emitter to Base Voltage	V _{EB0}	-5	V
Collector Current(DC)	I _c	-1	A
Collector Power Dissipation	P _D	1.2	W

Electrical Characteristics (Ta = 25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CB0}	-80	-	-	V	I _c =-10uA, I _E =0
BV _{CE0}	-80	-	-	V	I _c =-10mA, I _B =0
BV _{EB0}	-5	-	-	V	I _c =-10uA
I _{CB0}	-	-	-100	nA	V _{CB} =-60V
I _{EB0}	-	-	-100	nA	V _{EB} =-5V
*V _{CE(sat)1}	-	-	-150	mV	I _c =-150mA, I _B =-15mA
*V _{CE(sat)2}	-	-	-500	mV	I _c =-500mA, I _B =-50mA
*V _{BE(sat)1}	-	-	-900	mV	I _c =-150mA, I _B =-15mA
*V _{BE(sat)2}	-	-	-1.1	V	I _c =-500mA, I _B =-50mA
*h _{FE1}	75	-	-		V _{CE} =-5V, I _c =-0.1mA
*h _{FE2}	100	-	-		V _{CE} =-5V, I _c =-100mA
*h _{FE3}	70	-	-		V _{CE} =-5V, I _c =-500mA
*h _{FE4}	25	-	-		V _{CE} =-5V, I _c =-1A
f _T	100	-	-	MHz	V _{CE} =-10V, I _c =-50mA, f=100MHz
C _{ob}	-	-	20	pF	V _{CE} =-10V, I _E =0, f=1MHz

*Pulse Test:Pulse Width ≤380 us,Duty Cycle≤2% .

Characteristics Curve



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